Journal and Letters

MgSi_{x}Ge, compound semiconductors

1. Y. Noda, H. Kon, Y. Furukawa, N. Otsuka, I. Nishida, and K. Masumoto, “Preparation and thermoelectric properties of Mg2Si1-xGex (x=0.0~0.4) solid solution semiconductors,” Materials Transactions, JIM 33 (1992) 845-850.

Opto-Electronic Integrated circuit


InP MOVPE growth


InP DFB lasers, InP strained MQW lasers


InP Self-limiting Etching

InP Molecular Layer Epitaxy


GaN Blue Laser Diodes and Ultraviolet Light-Emitting Diodes

28. N. Otsuka, A. Tsujimura, Y. Hasegawa, G. Sugahara, M. Kume, and Y. Ban “Room Temperature 339 nm Emission from Al_{0.13}Ga_{0.87}N/Al_{0.10}Ga_{0.90}N Double Heterostructure Light-Emitting Diode on Sapphire Substrate”, Jpn. J. Appl. Phys, 39 (2000) L445.

29. N. Otsuka, A. Tsujimura, Y. Hasegawa, G. Sugahara, M. Kume, and Y. Ban “339 nm Deep-UV Emission from Al_{0.13}Ga_{0.87}N/Al_{0.10}Ga_{0.90}N Double Heterostructure Light-Emitting Diode on Sapphire Substrate”, Proc. Int. Workshop on Nitride Semiconductors, IPAP Conf.. Series 1 (2000) 837-840.


GaN Power Diodes, GaN MMICs


34. 大塚信之、永井秀一、上田大助 「第4章 パワーデバイスパッケージング技術」サイエンス＆テクノロジー, 2012, 239-262.

